## Secondary Side Synchronous Rectifier Controller for Flyback Converters

#### Description

The FAN6250M6X is a secondary–side synchronous rectifier (SR) controller for an isolated flyback converter operating in Discontinuous Conduction Mode (DCM). The adaptive dead time control algorithm minimizes the body diode conduction of SR MOSFET while guaranteeing stable and robust SR operation against noise and disturbance caused by the circuit parasitic.

Programmable thermal Shut–Down (SD) function that is informing primary side controller to shut–down the power system when pairing with PSR controller – FAN1080. The Dynamic Response Enhancement (DRE) function that minimizes system response time when pairing with PSR controller – FAN1080.

#### Features

- Works in Discontinuous Conduction Modes (DCM) and Boundary Conduction Modes (BCM)
- Adaptive Turn-off Trigger Blanking Time for Wide SR MOSFET Application
- Gate Turn-on Blanking Time (minimum Gate OFF Time)
- Dynamic Response Enhancement (DRE) Function that minimizes System Response Time
- Programmable Shut–Down (SD) Protection
- Minimum Turn-on Delay (20 ns)
- Input Voltage (VIN) Range for LDO Input: 3.25 V to 20 V
- Fewest External Components Allowed
- Accurate Turn Off Dead Time Regulation when working with PSR Power System
- Small Footprint: SOT-23 6 Pin
- This is a Pb–Free Device

#### **Typical Applications**

- Travel Adapter for Smart Phones, Feature Phones, and Tablet PCs
- AC-DC Adapters for Portable Devices that Require CV/CC Control

#### **ORDERING INFORMATION**

Part Number	Operating Temperature	Package	Packing Method <sup>†</sup>
FAN6250M6X	–40°C to 125°C	6 Lead, SOT23 (Pb–Free)	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D



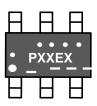
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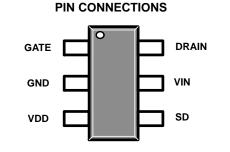


SOT-23, 6 Lead CASE 527AJ

#### MARKING DIAGRAM



	= Year Code
PXX	= 250 : FAN6250
ΕX	= Die Run Code
	= Date Code



1

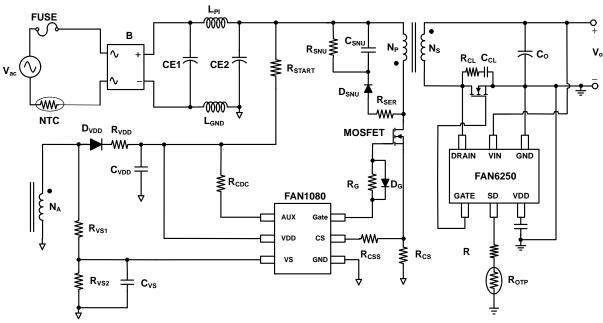


Figure 1. FAN6250 Typical Application Schematic

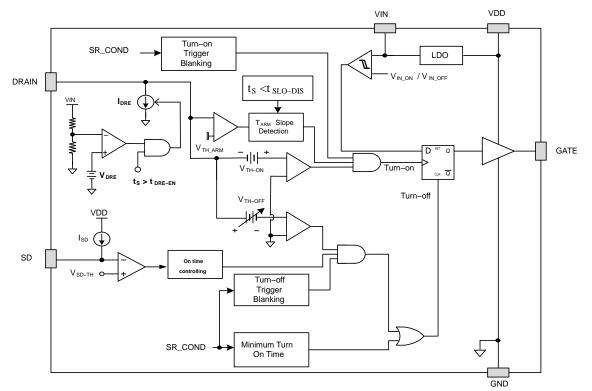


Figure 2. FAN6250 Function Block Diagram

#### Table 1. PIN FUNCTION DESCRIPTION

Pin #	Name	Description
1	GATE	Gate drive output
2	GND	Ground
3	VDD	Internal regulator 5 V output and gate drive power supply. Bypass with a 1uF capacitor to GND.
4	SD	Shut–Down pin. This pin is implemented for external over-temperature-protect by connecting the NTC thermistor.
5	VIN	Input Voltage Pin. This pin is connected to the output of the adaptor to monitor its output voltage and supply inter- nal bias. IC operating current and MOSFET gate drive current is supplied through this pin.
6	DRAIN	Synchronous rectifier drain sense input.

#### Table 2. ABSOLUTE MAXIMUM RATINGS (Notes 1, 2, 3)

Parar	neter	Symbol	Value	Unit
Power Supply Input Pin Voltage	V <sub>IN</sub>	-0.3 to 20	V	
Internal Regulator Output Pin Voltage	V <sub>DD</sub>	-0.3 to 6.5	V	
Drain Sense Input Pin Voltage	Drain Sense Input Pin Voltage			V
Gate Drive Output Pin Voltage	V <sub>GATE</sub>	-0.3 to 6.5	V	
Shut–Down Pin Voltage	V <sub>SD</sub>	-0.3 to 6.5	V	
Sense Pin Voltage	V <sub>SNS</sub>	-0.3 to 6.5	V	
Power Dissipation ( $T_A = 25^{\circ}C$ )	PD	0.446	W	
Operating Junction Temperature		TJ	-40 to 125	°C
Storage Temperature Range		T <sub>STG</sub>	-60 to 150	°C
Lead Temperature (Soldering) 10 Seconds     Electrostatic Discharge Capability   Charged Device Model (CDM)     Human Body Model (HBM)		TL	260	°C
		ESD	> 0.5	kV
			> 2	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. All voltage values, except differential voltages, are given with respect to the GND pin.

2. Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device.

3. Meets JEDEC standards JS-001-2012 and JESD 22-C101.

#### Table 3. THERMAL CHARACTERISTICS (T<sub>A</sub> = $25^{\circ}$ C unless otherwise specified)

Parameter	Symbol	Min	Unit
Junction-to-Ambient Thermal Impedance	$\theta_{JA}$	218.2	°C/W
Junction-to-Top Thermal Impedance	$\theta_{JT}$	31.3	°C/W

#### Table 4. RECOMMENDED OPERATING RANGES

Parameter	Symbol	Min	Max	Unit
Drain Pin Voltage	V <sub>DRAIN</sub>		60	V
VDD Pin Voltage	V <sub>DD</sub>	3.1	5.5	V
VIN Pin Voltage	V <sub>IN</sub>	3.25	20	V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

### Table 5. ELECTRICAL CHARACTERISTICS

 $V_{IN}$  = 5.5 V and  $T_A$  = –40 to 125°C unless noted otherwise

Parameter	Test Conditions	Symbol	Min	Тур	Max	Unit
VDD Section						
Turn–On Threshold	V <sub>IN</sub> rising	V <sub>IN–ON</sub>	3.06	3.15	3.25	V
Turn–Off Threshold	V <sub>IN</sub> falling	V <sub>IN-OFF</sub>	2.78	2.9	3.05	V
Operating Current	$\rm f_{SW}$ = 100 kHz, $\rm C_{GATE}$ = 3.3 nF, $\rm V_{IN}$ = 5 V	I <sub>IN-OP</sub>		2.0	2.8	mA
Power Supply Section						
Internal LDO Output Voltage	V <sub>IN</sub> = 20 V	V <sub>DD</sub>	5.0	5.25	5.5	V
Dropout Voltage of LDO	$I_{OUT}$ = 10 mA, $V_{IN}$ = 3.3 V	V <sub>DO</sub>			0.3	V
Drain Voltage Sensing Section						
Comparator Input Offset Voltage	Internal design suggestion	V <sub>OSI</sub> <sup>(4)</sup>	-1	0	1	mV
Turn–On Threshold Voltage	$R_{DRAIN} = 0 \Omega$ (includes comparator input offset voltage)	V <sub>TH-ON</sub>	-250	-200	-150	mV
Slope detection disable criteria		t <sub>SLO-DIS</sub> <sup>(6)</sup>	53	58	63	μs
Slope detection disable criteria Hysteresis		t <sub>SLO-HYS</sub> <sup>(4)</sup>		8		μs
Turn on delay	With 50 mV overdrive From $V_{TH_ON}$ to Gate > 1 V	t <sub>ON-DLY</sub> <sup>(4)</sup>		20		ns
Turn–Off Threshold Tuning Range 1		V <sub>TH-OFF</sub>	-5		5	mV
Comparator delay for V <sub>TH.OFF1</sub>	With 0mV overdrive From V <sub>TH_OFF</sub> to Gate = 1 V	t <sub>OFF-DLY</sub> <sup>(4)</sup>		20		ns
Gate Re-arming threshold	VIN = 5 V (Typically 0.7V <sub>DD</sub> )	V <sub>TH-ARM</sub>	3.3	3.5	3.7	V
Gate Re–arming time for slope detection		t <sub>ARM</sub> <sup>(4)</sup>	70	85	100	ns
Slope detection high threshold		V <sub>TH–HGH</sub> <sup>(4)</sup>	0.4	0.5	0.6	V
Minimum On-Time and Minimum OFF-t	ime Section					
Minimum On-Time		t <sub>ON-MIN</sub>	2.16	2.4	2.64	μs
Minimum On-Time Upper at light load		t <sub>ON-MIN-L</sub>	1.50	1.65	1.80	μs
Minimum t <sub>ON</sub> cycles during start-up		N <sub>ON-MIN-ST</sub>		3		cycles
Minimum Off-Time		t <sub>OFF-MIN-L</sub> <sup>(5)</sup>	1.53	1.70	1.87	μs
Minimum Off–Time at light load $(t_{S} > t_{SLO-DIS})$		t <sub>OFF-MIN-H</sub> <sup>(5)</sup>	3.6	4	4.4	μs
Dead Time Control Section						
Dead time self-tuning target	From GATE OFF to $V_{\mbox{DRAIN}}$ rising above 0.5 V	t <sub>DEAD</sub> <sup>(4)</sup>	170	200	230	ns
DRE Section						
VIN pin DRE function trigger level		V <sub>DRE</sub> <sup>(5)</sup>	4.68	4.78	4.85	V
Threshold voltage for DRE function		V <sub>DREI</sub>	1.188	1.200	1.212	V
Drain Pin sinking current period when DRE triggered		t <sub>DREI</sub> <sup>(4)</sup>	1.2	1.5	1.8	μs
DRE function enable period		t <sub>DRE-EN</sub>	64	72	80	μs
IDRE re-arm period		t <sub>RE-ARM</sub>		4		μs
Drain Pin sinking current when DRE triggered		I <sub>DRE</sub>	50			mA

### Table 5. ELECTRICAL CHARACTERISTICS (continued)

 $V_{IN}$  = 5.5 V and  $T_A$  = –40 to 125°C unless noted otherwise

Parameter	Test Conditions	Symbol	Min	Тур	Max	Unit
Shut-Down Section						
Threshold voltage for Shut–Down function triggered		V <sub>SD-TH</sub>	0.97	1.00	1.03	V
Shut–Down current source		I <sub>SD-TH</sub>	44	50	56	μΑ
Impedance for Shut–Down trigger		Z <sub>SD-TH</sub>	18.48	20.00	21.68	kΩ
Denounce Cycles for Shut–Down		N <sub>SD-Debounce</sub>		7		Cycles
Output Driver Section						
Output Voltage Low	V <sub>IN</sub> = 6 V	V <sub>OL</sub>			0.25	V
Output Voltage High	V <sub>IN</sub> = 6 V	V <sub>OH</sub>	4.9			V
Rise Time	$V_{IN} = 6 V$ , $C_L = 3300 pF$ , GATE = 1 V ~ 4 V	t <sub>R</sub>			90	ns
Fall Time	V <sub>IN</sub> = 6 V, C <sub>L</sub> = 3300 pF, GATE = 4 V ~ 1 V	t <sub>F</sub>			30	ns

Guaranteed by Design.
Specification operation temperature range -5°C ~ 85°C
Specification operation temperature range -5°C ~ 50°C

### **TYPICAL PERFORMANCE CHARACTERISTICS**

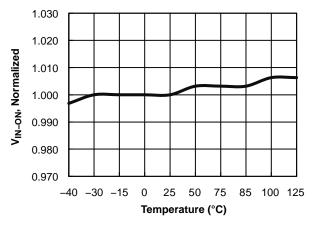
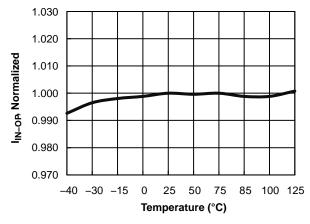
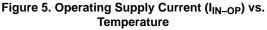
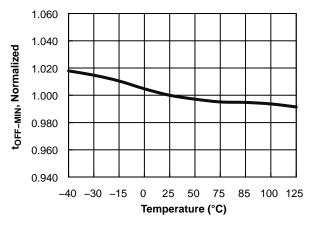
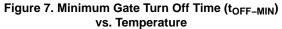


Figure 3. Turn–On Threshold Voltage ( $V_{IN-ON}$ ) vs. Temperature









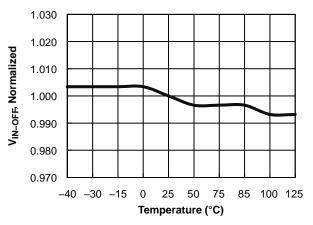


Figure 4. Turn–Off Threshold Voltage ( $V_{IN-OFF}$ ) vs. Temperature

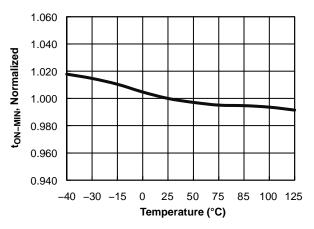
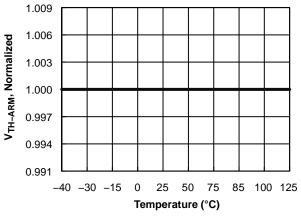
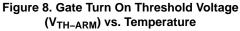
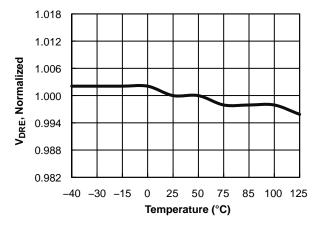


Figure 6. Minimum On Time ( $t_{ON-MIN}$ ) vs. Temperature









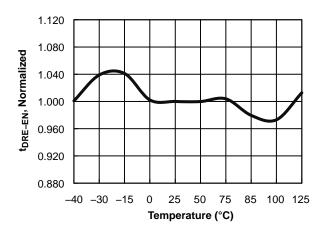


Figure 11. DRE Function Enable Period (t<sub>DRE-EN</sub>) vs. Temperature

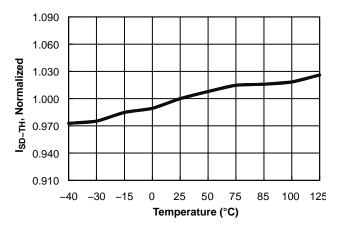


Figure 13. Shut–Down Current Source (I<sub>SD–TH</sub>) vs. Temperature

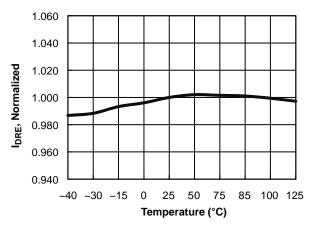


Figure 10. Drain Pin Sinking Current for DRE Triggered (I<sub>DRE</sub>) vs. Temperature

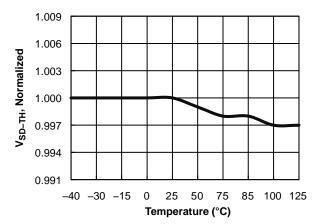
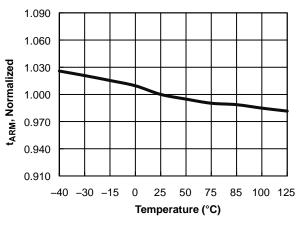
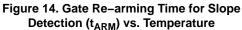
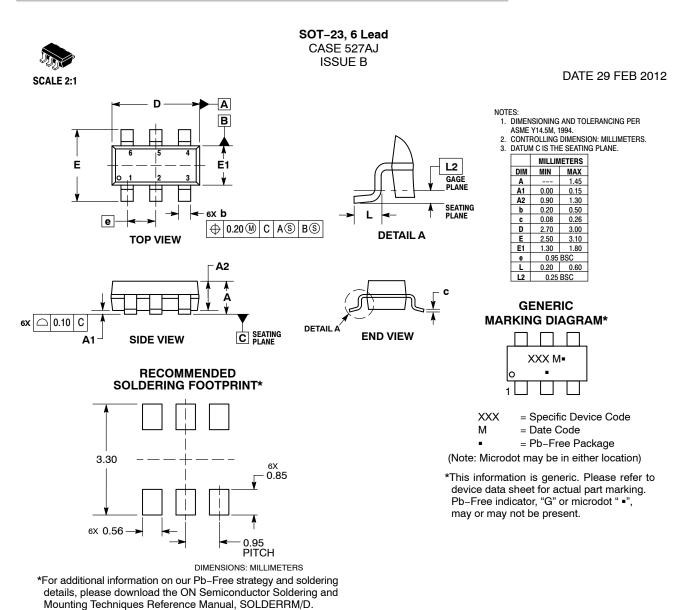


Figure 12. Shut–Down Threshold Voltage (V<sub>SD–TH</sub>) vs. Temperature









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